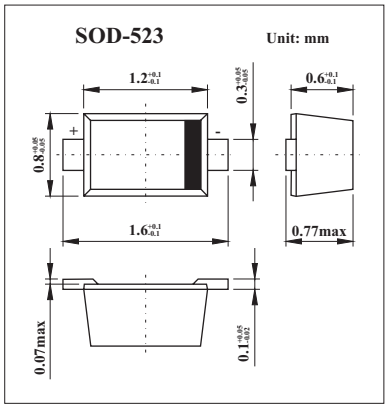
General purpose PIN diode

BAP51-02



Features

- Low diode capacitance
- Low diode forward resistance.

Absolute Maximum Ratings Ta = 25℃

Parameter	Symbol	Min	Max	Unit
continuous reverse voltage	V_R		50	V
continuous forward current	I_F		50	mA
total power dissipation Ts = 90℃	P_{tot}		715	mW
storage temperature	T_{stg}	-65	+150	℃
junction temperature	T_j	-65	+150	℃
thermal resistance from junction to soldering point	$R_{th\ j\text{-}s}$		85	K/W

Electrical Characteristics Ta = 25℃

Parameter	Symbol	Conditions	Min	Typ	Max	Unit
forward voltage	V_F	I_F = 50 mA		0.95	1.1	V
reverse voltage	V_R	I_R = 10 μA	50			V
reverse current	I_R	V_R = 50 V			100	nA
diode capacitance	C_d	V_R = 0; f = 1 MHz		0.4		pF
		V_R = 1 V; f = 1 MHz		0.3	0.55	
		V_R = 5 V; f = 1 MHz		0.2	0.35	
diode forward resistance	r_D	I_F = 0.5 mA; f = 100 MHz; note 1		5.5	9	Ω
		I_F = 1 mA; f = 100 MHz; note 1		3.6	6.5	
		I_F = 10 mA; f = 100 MHz; note 1		1.5	2.5	

Note

1. Guaranteed on AQL basis: inspection level S4, AQL 1.0.

Marking

Marking	A5